

Schottky barrier diode

RB520S-30

●Applications

Low current rectification

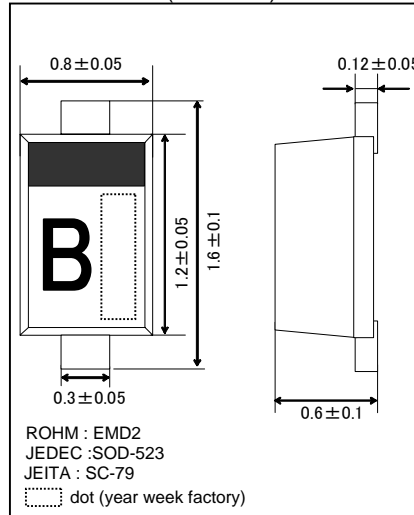
●Features

- 1) Ultra Small mold type. (EMD2)
- 2) Low I_R .
- 3) High reliability.

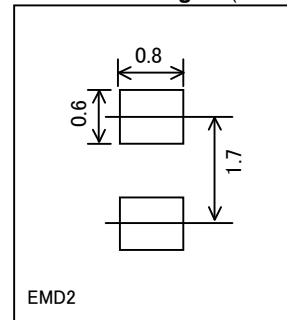
●Construction

Silicon epitaxial planar

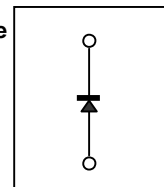
●Dimensions (Unit : mm)



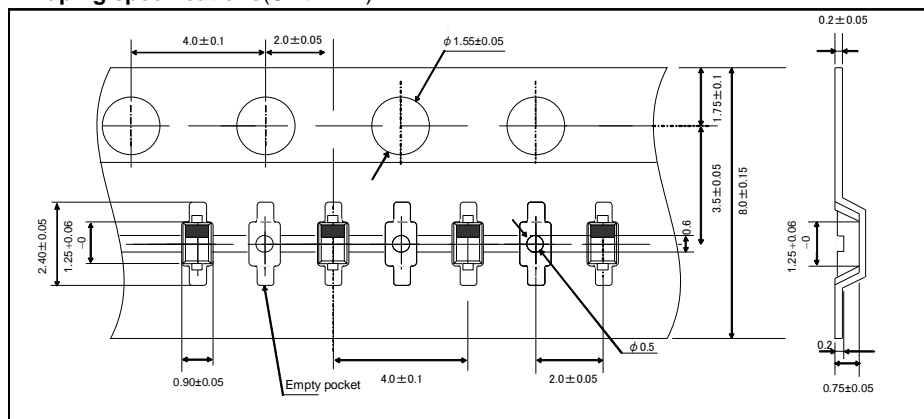
●Land size figure (Unit : mm)



●Structure



●Taping specifications (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	200	mA
Forward current surge peak (60Hz · 1cyc)	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.6	V	$I_F=200mA$
Reverse current	I_R	-	-	1	μA	$V_R=10V$

